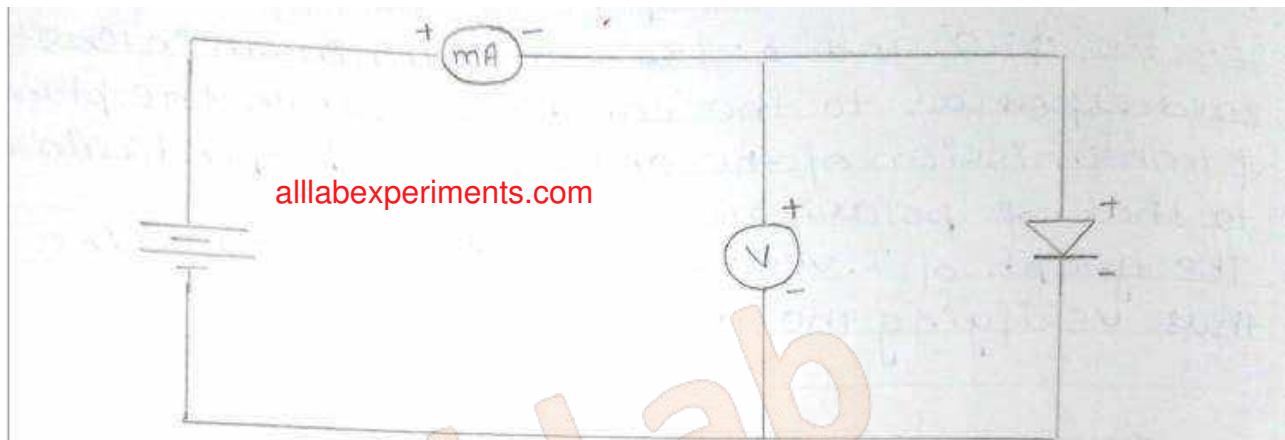


To determine the value of Boltzmann constant using semiconductor diode



Room Temp? Room temperature =  $25^{\circ}\text{C}$

Observations:

Least count of voltmeter =  $0.1\text{ V}$

Least count of milliammeter =  $1\text{ mA}$

Least count of microammeter =  $1\mu\text{A}$

Forward bias

Voltage (V)	Current (mA)	I Current (A)	$\log_{10} I$
0.20	0	0	
0.30	0	0	
0.40	0	0	
0.50	0	0	
0.60	2	0.002	-2.698
0.62	4	0.004	-2.397
0.64	7	0.007	-2.154
0.68	11	0.011	-1.958
0.70	18	0.018	-1.744
0.72	28	0.028	-1.552
0.74	41	0.041	-1.387

**Aim:** To determine the value of Boltzmann's constant using a semiconductor diode.

**Apparatus:** A p-n junction diode, a DC power supply, a milliammeter, a voltmeter and connecting wires.

[alllabexperiments.com](http://alllabexperiments.com)

**Theory:** When a positive potential is applied to the p-side of a p-n junction diode with respect to its n-side, the diode is said to be forward biased. If  $V$  is the voltage across the junction, the current through diode  $I$  is given by

$$I = I_s \left[ \exp \frac{qV}{nKT} - 1 \right]$$

where  $I_s$  is reverse saturation current. For Si  $n=2$  and for Ge  $n=1$ .

For silicon diode at room temperature reduces to  $I = I_s \left[ \exp (19.3V) - 1 \right]$

where  $V$  is voltage across diodes in volts.

$$I = I_s \left[ \exp \left( \frac{qV}{nKT} \right) \right]$$

$$\log_{10} I = \log_{10} I_s + \frac{qV}{2.303nKT}$$

So a plot of  $\log_{10} I$  versus  $V$  gives  $\frac{q}{2.303nKT}$  as

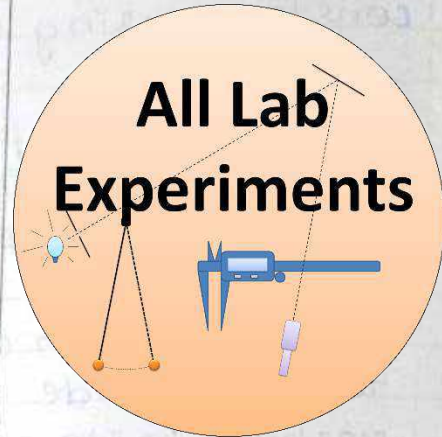
the slope from which Boltzmann constant  $k$  can be evaluated.



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## Reverse bias

Voltage (V)	Current (μA)
0.1	41
0.2	45
0.3	53
0.4	58
0.5	63
0.6	70
0.7	76
0.8	83
0.9	88
1.0	100



Calculation:

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$$\text{Slope} = \frac{-1.5 - (-2.45)}{0.725 - 0.614} = 8.5585$$

$$k = \frac{11.59 \times 10^{-23}}{\text{Slope}} = \frac{11.59 \times 10^{-23}}{8.5585}$$

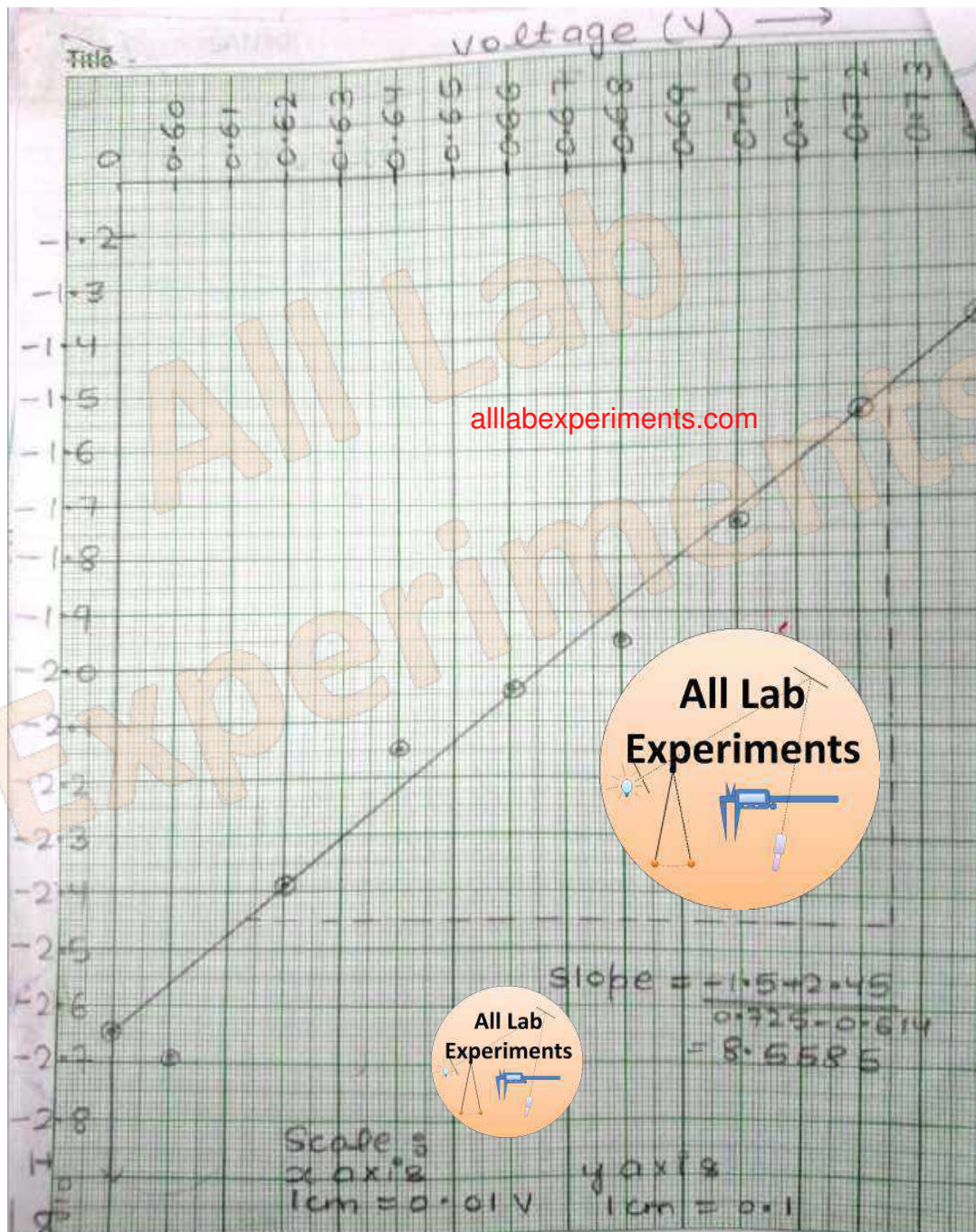
$$k = 1.3542 \times 10^{-23}$$

$$k = \frac{q}{2.303nT} \times \frac{1}{\text{Slope}} = \frac{1.6 \times 10^{-19}}{2.303 \times 2 \times 298 \times 8.5585}$$

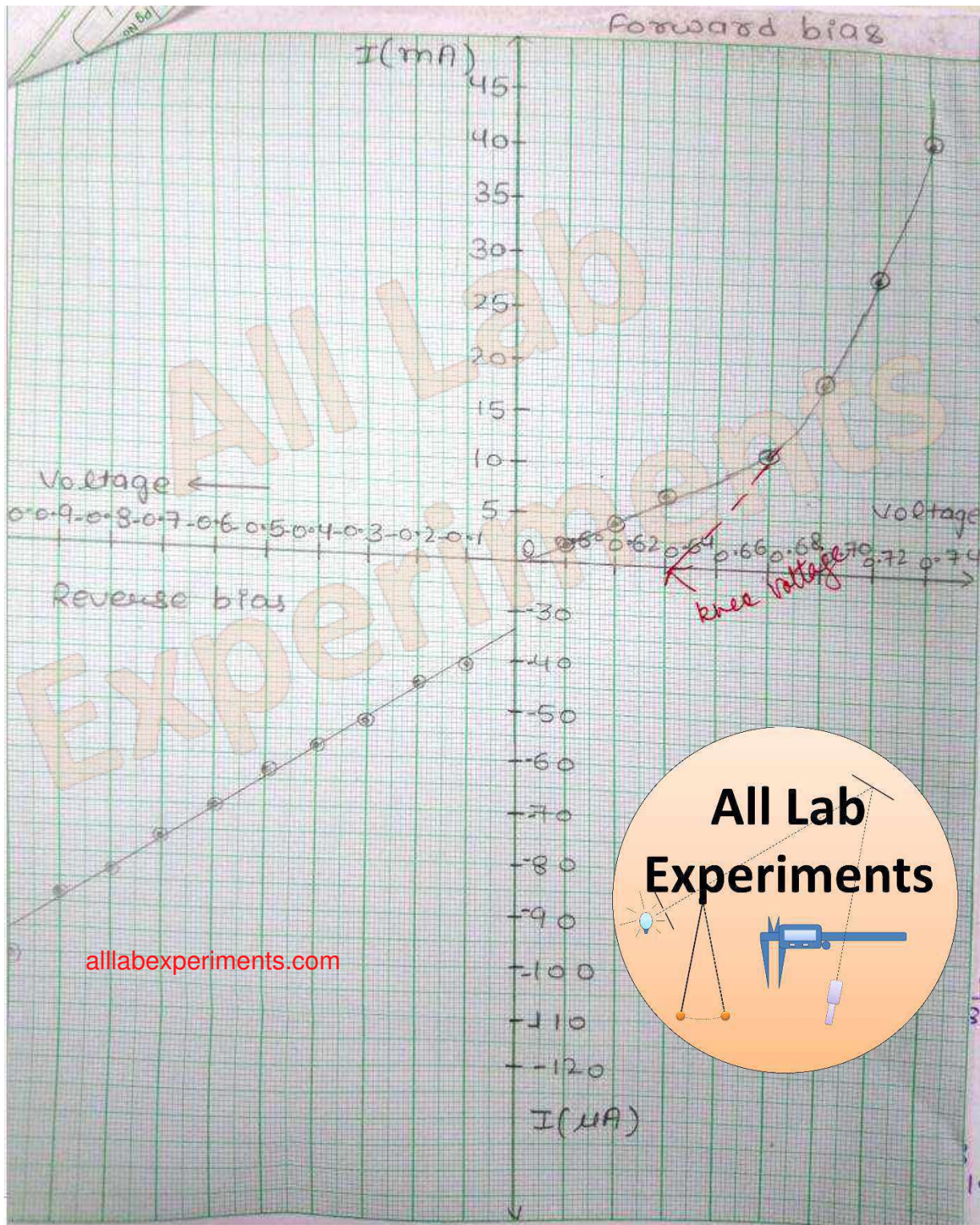
$$k = 1.362 \times 10^{-23} \text{ J/K}$$

$$\text{Percentage error} = \frac{(1.362 - 1.38) \times 10^{-23}}{1.38 \times 10^{-23}} \times 100$$

$$= 1.3\%$$



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1. connect the circuit. [alllabexperiments.com](http://alllabexperiments.com)

2. Slowly increase input voltage in steps and note the voltage across diode and current  $I$  through it. Take readings till the current is about 20 mA.

3. Plot a graph between  $V$  along x-axis and  $\log_{10} I$  along y-axis.

Result: Experimentally determined value of Boltzmann's constant =  $1.3622 \times 10^{-23} \text{ JK}^{-1}$   
Standard value =  $1.38 \times 10^{-23} \text{ JK}^{-1}$   
% Error = 1.43 %

Precautions and Sources of Error:

1. Ensure that p-side is made positive w.r.t n side.
2. Increase supply voltage slowly from zero.
3. It should be remembered that  $n=1$  for germanium diode and  $n=2$  for silicon diode.



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